## AMENDMENTS TO THE CLAIMS

- 1. (Original) A method of producing a piezoelectric ceramic thick film on a substrate, said method comprising:
  - providing a piezoelectric ceramic material in powder form;
  - forming a liquid mixture by mixing the powdered material with a liquid phase precursor of a metal oxide of low-melting point, said precursor being adapted to decompose, upon subsequent annealing, into the metal oxide;
  - drying the liquid mixture to form a precipitate;
  - milling the precipitate to form a powdered precipitate;
  - adding an organic carrier to the powdered precipitate;
  - further milling the precipitate to form a paste;
  - depositing a layer of the paste, as a wet film, onto the substrate; and
  - annealing the layered substrate at a temperature and for a time sufficient to cause transformation of the paste into the thick film.
- 2. (Original) A method according to claim 1, wherein the piezoelectric ceramic material is an inorganic ceramic material which exhibits the piezoelectric effect.
- 3. (Original) A method according to claim 2, wherein the piezoelectric ceramic material is lead zirconate titanate (PZT).
- 4. (Original) A method according to claim 1, wherein the metal oxide is adapted to form a glass phase upon annealing at elevated temperature.
- 5. (Original) A method according to claim 4, where in the metal oxide is selected from one or more of Li<sub>2</sub>O, Bi<sub>2</sub>O<sub>3</sub> and PbO.
- 6. (Original) A method according to claim 5, wherein the liquid phase precursor is a combination of the liquid phase precursors of Li<sub>2</sub>O and Bi<sub>2</sub>O<sub>3</sub>.
- 7. (Currently Amended) A method according to claim 5 or claim 6, wherein the liquid phase precursor of Li<sub>2</sub>O is lithium ethoxide dissolved in ethanol.

- 8. (Currently Amended) A method according to claim 5 or claim 6, wherein the liquid phase precursor of Bi<sub>2</sub>O<sub>3</sub> is bismuth nitrate dissolved in acetic acid.
- 9. (Currently Amended) A method according to any one of claims 6 to 8 claim 6, wherein the liquid phase precursors of Li<sub>2</sub>O and Bi<sub>2</sub>O<sub>3</sub> are mixed to form a Li-Bi acetic acid solution.
- 10. (Original) A method according to claim 5, wherein the metal oxide is PbO and the liquid phase precursor is a solution of lead acetate.
- 11. (Currently Amended) A method according to any one of claims 1 to 10 claim 1, wherein the powdered piezoelectric material is in the form of a suspension in ethanol.
- 12. (Original) A method according to claim 11, wherein the powdered piezoelectric material is fine-grained having an average grain size of below about 1.0µm.
- 13. (Original) A method according to claim 12, wherein the average grain size is about 0.5µm.
- 14. (Currently Amended) A method according to any one of claims 1 to 13 claim 1, wherein the total amount of the metal oxide in the thick film is between about 1% and 5%, by weight.
- 15. (Original) A method according to claim 11, wherein the suspension is mixed with the Li-Bi acetic acid solution, or the lead acetate solution, to form a liquid mixture.
- 16. (Original) A method according to claim 15, wherein the liquid mixture is dried at an elevated temperature to form a dried precipitate.
- 17. (Original) A method according to claim 16, wherein the liquid mixture is dried at a temperature between about 75°C and 105°C for up to 10 hours.
- 18. (Currently Amended) A method according to claim 16 or claim 17, wherein the dried precipitate is formed into a powdered precipitate.
- 19. (Original) A method according to claim 18, wherein the powdered precipitate is formed by milling the dried precipitate with a ball mill.
- 20. (Currently Amended) A method according to claim 18 or claim 19, wherein an organic carrier is added to the powdered precipitate.

- 21. (Original) A method according to claim 20, wherein the organic carrier is selected from one or more of ethyl cellulose, terpineol, and ESL 400 organic binder.
- 22. (Original) A method according to claim 21, wherein the organic carrier is ESL 400 organic binder.
- 23. (Currently Amended) A method according to any one of claims 18 to 22 claim 18, wherein the powdered precipitate and organic carrier are milled to form a paste.
- 24. (Original) A method according to claim 23, wherein the paste is deposited onto a surface of the substrate, by a printing process, as a wet film.
- 25. (Original) A method according to claim 24, wherein the printing process is a screen printing process.
- 26. (Currently Amended) A method according to any one of claims 1 to 25 claim 1, wherein, prior to annealing, the layered substrate is dried.
- 27. (Currently Amended) A method according to any one of claims 1 to 25 claim 1, wherein, prior to annealing, an isostatic pressure is applied to the film.
- 28. (Original) A method according to claim 26, wherein the drying temperature is between about 20°C and about 175°C.
- 29. (Currently Amended) A method according to any one of claims 1 to 28 claim 1 wherein the layered substrate is annealed at a temperature of between about 800°C and about 1000°C.
- 30. (Original) A method according to claim 29, wherein the annealing is conducted for between about 10 minutes and about 4 hours.
- 31. (Currently Amended) A method according to any one of claims 1 to 30 claim 1, wherein the substrate is formed of silicon.
- 32. (Currently Amended) A method according to any one of claims 1 to 31 claim 1, wherein the surface of the substrate has a coating of platinum and the paste is deposited on this platinum coating.
- 33. (Currently Amended) A method according to any one of claims 1 to 32 claim 1, wherein a metal electrode is formed on the piezoelectric ceramic thick film.

- 34. (Original) A method according to claim 33, wherein the metal is silver and the electrode material is deposited on the film by a screen printing process.
- 35. (Original) A method according to claim 34, wherein the layered substrate is fired at elevated temperature to form the electrode.
- 36. (Original) A method of producing a piezoelectric ceramic thick film on a substrate, said method being substantially as hereinbefore described with reference to Figure 1 and Example 1 or to Example 2.
- 37. (Currently Amended) A substrate having a piezoelectric ceramic thick film thereon, formed according to the method of any one of claims 1 to 36 claim 1.
- 38. (Currently Amended) A piezoelectric sensor or actuator having a piezoelectric ceramic thick film, wherein said thick film has been formed on said substrate according to the method of any one of claims 1 to 36 claim 1.